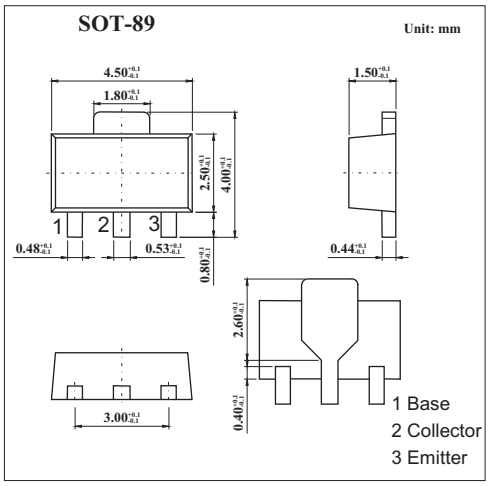
Epitaxial Planar PNP Transistor

KTA1664

Features

Collector Power Dissipation: P_C=500mW

Collector Current:I_C=-800mA



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
	P_C*	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	℃

*KTA1664 mounted on ceramic substrate (250mm2x0.8t)

KTA1664

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA, I_E=0	-35			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5.0			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-35V, I_E=0			-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-100	nA
DC Current Gain	h_{FE}	V_{CE}=-1V, I_C=-100mA	100		320	
		V_{CE}=-1V, I_C=-700mA	35			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-20mA			-0.7	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1V, I_C=-10mA	-0.5		-0.8	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		19		pF

h_{FE} Classification

Marking	RO	RY
Rank	O	Y
Range	100 200	160 320